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(71)Applicant : DAICEL CHEM IND LTD

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(72)Inventor : NAKANO TATSUYA
FUNAKI KATSUNORI

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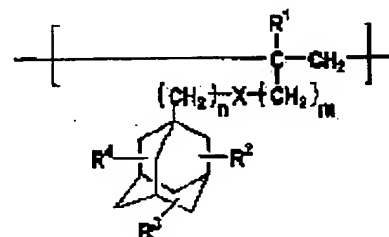
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(54) COMPOUND FOR PHOTORESIST AND RESIN COMPOSITION FOR PHOTORESIST

(57)Abstract:

PROBLEM TO BE SOLVED: To form a fine pattern by using a resin composition for a photoresist having high etching solution resistance and capable of being solubilized by photoirradiation.

SOLUTION: The resin composition for a photoresist comprises a polymer having an adamantane skeleton of the formula and a photo-acid generating agent. In the formula, R¹ is H or methyl, R²-R⁴ are mutually the same or different and are each H, a halogen, alkyl, hydroxyl, hydroxymethyl, carboxyl and a functional group which is released by an acid and forms hydroxyl, hydroxymethyl or carboxyl, at least one of R²-R⁴ is the functional group, X is an ester or amino bond and (m) and (n) are each 0 or 1.



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